

FEATURES

Complementary Type The NPN Transistor
MMBT3904 is Recommended
Epitaxial Planar Die Construction



MARKING: 2A

MAXIMUM RATINGS ($T_a=25$ unless otherwise noted)

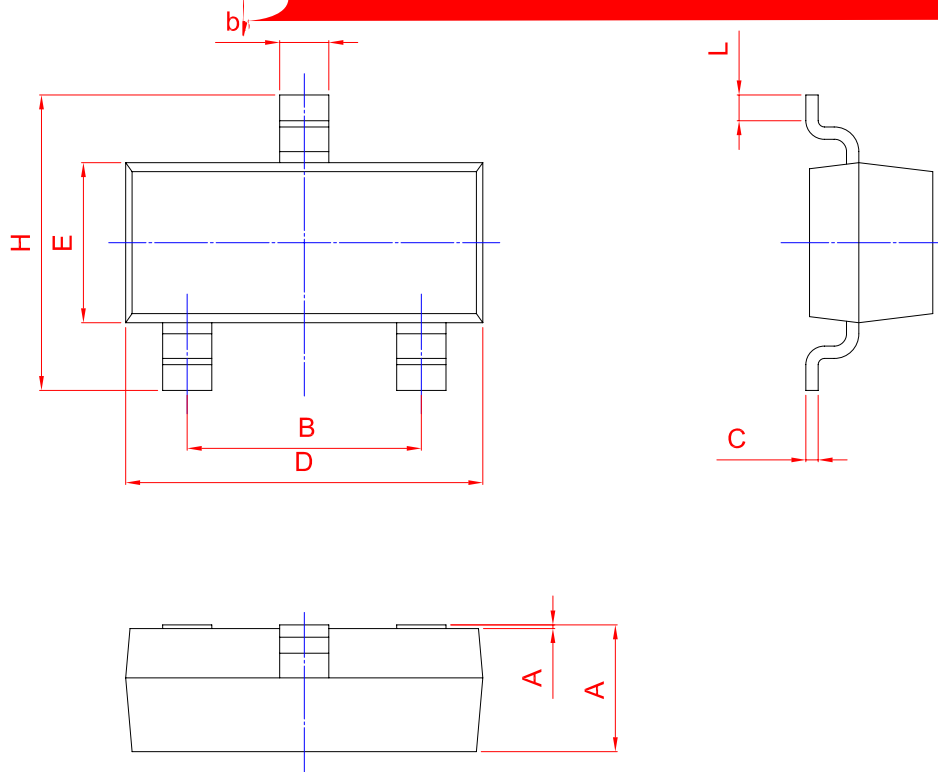
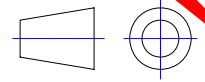
Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-40	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-200	mA
P_C	Total Device Dissipation	200	mW
R_{JA}	Thermal Resistance Junction to Ambient	625	/W
T_J	Junction Temperature	150	
T_{stg}	Storage Temperature	-55 ~ +150	

ELECTRICAL CHARACTERISTICS ($T_a=25$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-10\mu A, I_E=0$	-40		V

Typical Characteristics

The diagram consists of two groups of vertical dotted lines. The first group on the left contains four parallel vertical lines. The second group on the right contains three parallel vertical lines, with a small vertical tick mark at the bottom of the rightmost line.



UNIT	A		b_p	C	D	E	H_E	A_1	L_p
mm	1.40 0.95		0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20